

V_{DSS} , 30V R_{DS(ON)} , 5.4mΩ (max.) @ V_{GS}=10V R_{DS(ON)} , 8.2mΩ (max.) @ V_{GS}=4.5V I_D , 85A	TO-252	

Description	Features
<p>The SG30N04D uses advanced Trench technology and designs to provide excellent R_{DS(ON)} with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.</p>	<ul style="list-style-type: none"> • Low On-Resistance • Low Input Capacitance • Low Miller Charge • Low Input / Output Leakage • Pb-free lead plating; RoHS compliant
	Applications
	<ul style="list-style-type: none"> • Motor / Body Load Control • Load Switch • DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG30N04D	Halogen-Free	TO-252	D	Tape & Reel	2,500

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	T _C =25°C	85
		T _C =100°C	54
Drain Current-Pulsed ^{Note 1}	I _{DM}	170	A
Drain Current-Continuous	I _D	T _A =25°C	15
		T _A =70°C	12
Avalanche Current	I _{AS}	50	A
Avalanche Energy, L=0.1mH	E _{AS}	125	mJ
Maximum Power Dissipation	P _D	T _C =25°C	59
		T _C =100°C	23
		T _A =25°C	2
		T _A =70°C	0.8
Operating Junction Temperature Range	T _J T _{STG}	-55 to +175	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Maximum Junction-to-Ambient	R _{θJA}	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	R _{θJC}	Steady State	-	-	2.1	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250μA	1.2	-	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =30A	-	-	5.4	mΩ
Drain-Source On-State Resistance		V _{GS} =4.5V, I _{DS} =15A	-	-	8.2	

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	-	2249	-	pF
Output Capacitance	C _{oss}		-	261	-	
Reverse Transfer Capacitance	C _{rss}		-	205	-	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.7	-	Ω

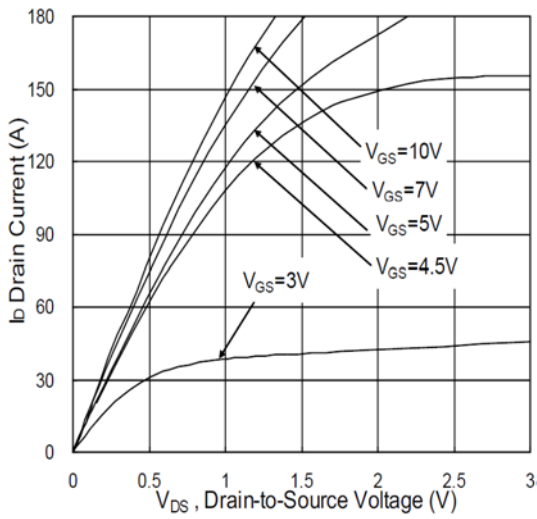
SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Turn-On Delay Time	T _{d(on)}	V _{DD} =15V, I _D =10A, V _{GS} =10V, R _g =3.3Ω	-	7.6	-	ns
Rise Time	t _r		-	14	-	
Turn-Off Delay Time	T _{d(off)}		-	36.5	-	
Fall Time	t _f		-	10.3	-	
Total Gate Charge	Q _g	V _{DS} =15V, I _{DS} =10A, V _{GS} =4.5V	-	19.6	-	nC
Gate to Source Gate Charge	Q _{gs}		-	7.4	-	
Gate to Drain "Miller" Charge	Q _{gd}		-	7	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Maximum Body-Diode Continuous Current	I _S	V _G =V _D =0V, Force Current	-	-	85	A
Pulsed Source Current	I _{SM}	V _G =V _D =0V, Force Current	-	-	170	A
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	V _{DD} =15V, I _F =30A, di/dt=100A/μs	-	14	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}	V _{DD} =15V, I _F =30A, di/dt=100A/μs	-	4	-	nC

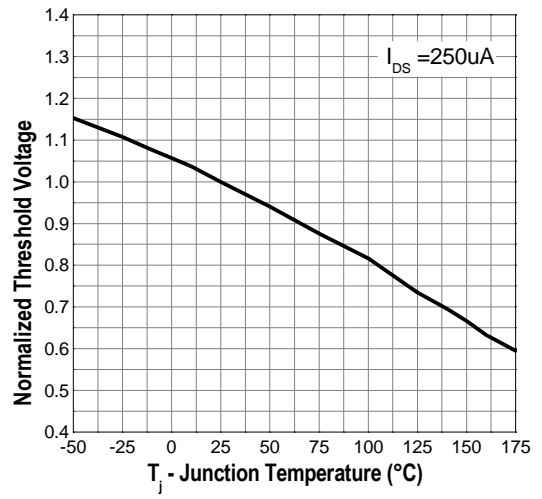
- Notes:**
1. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
 2. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θJA} is determined by the user's board design. R_{θJA} shown below for single device operation on FR-4 in still air.

Typical Operating Characteristics

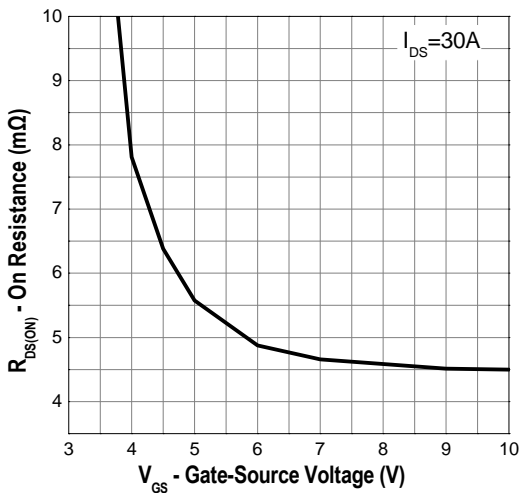
Output Characteristics



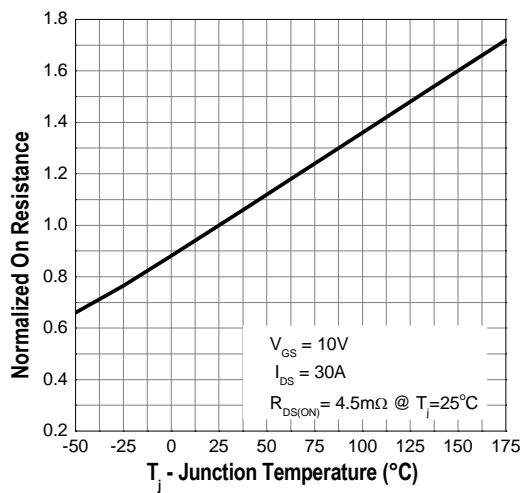
Gate Threshold Voltage



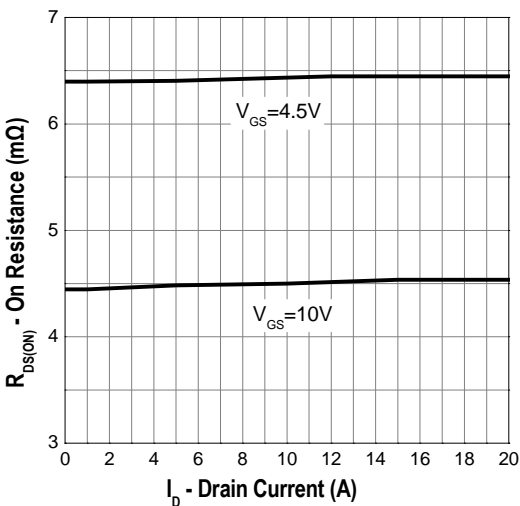
Gate-Source On Resistance



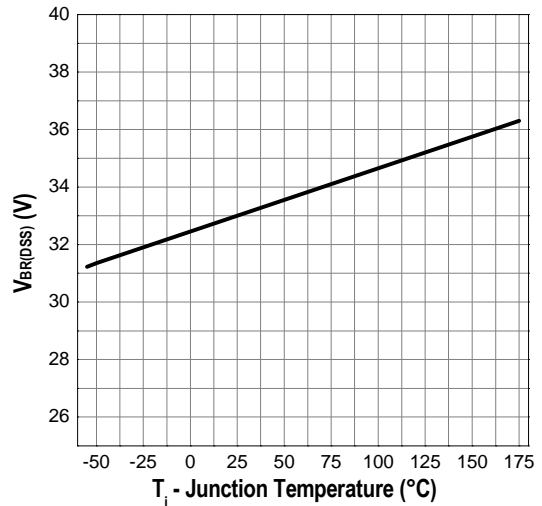
Drain-Source On Resistance



Drain-Source On Resistance

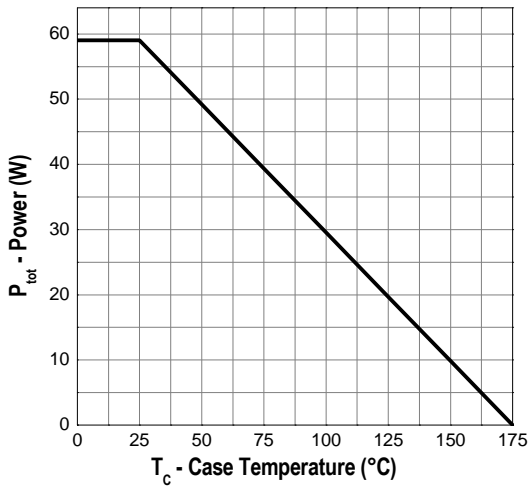


Drain-source Breakdown Voltage

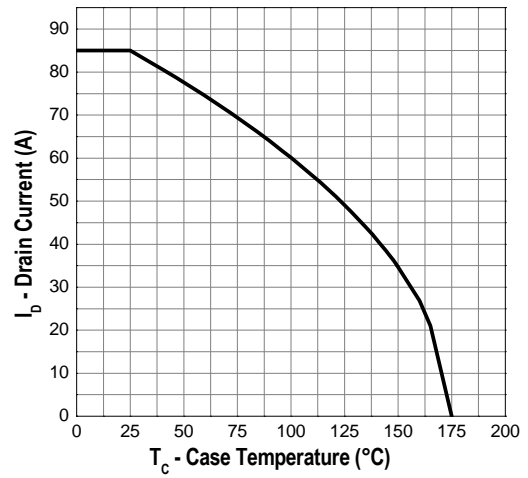


Typical Operating Characteristics (Cont.)

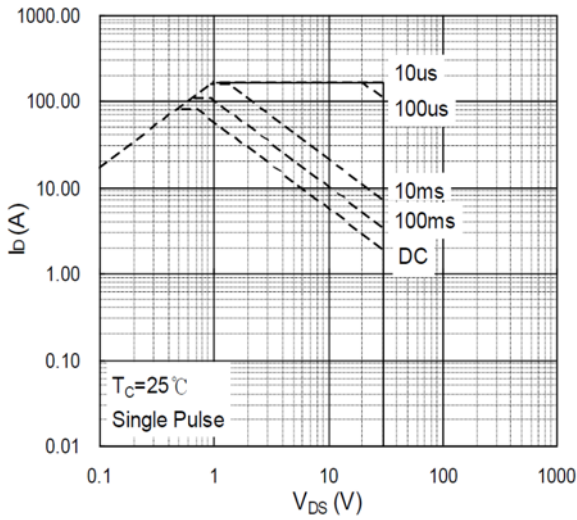
Power Dissipation



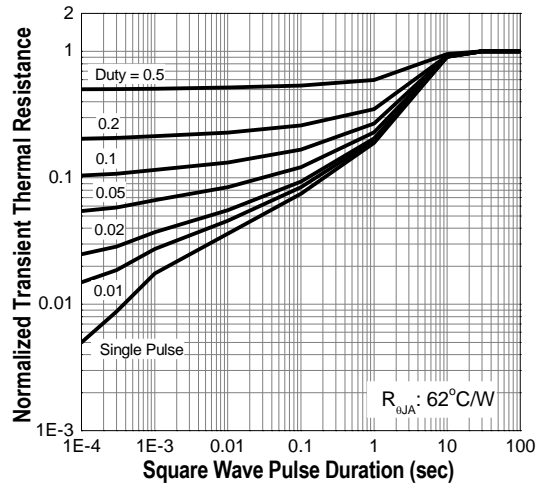
Drain Current



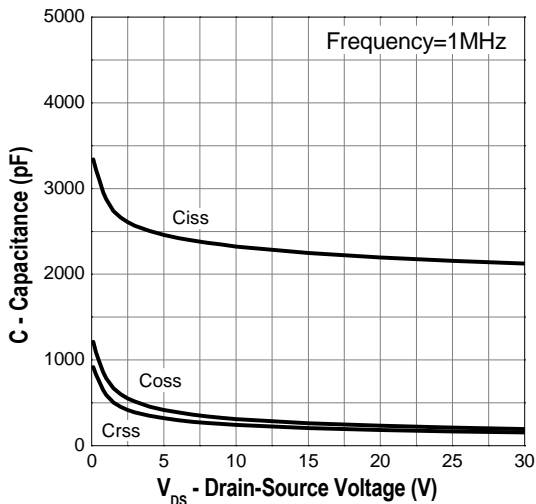
Safe Operation Area



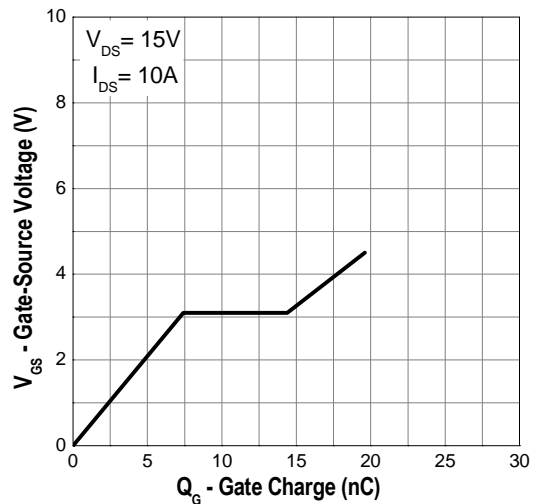
Transient Thermal Impedance



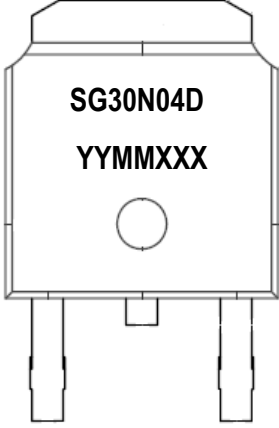
Capacitance



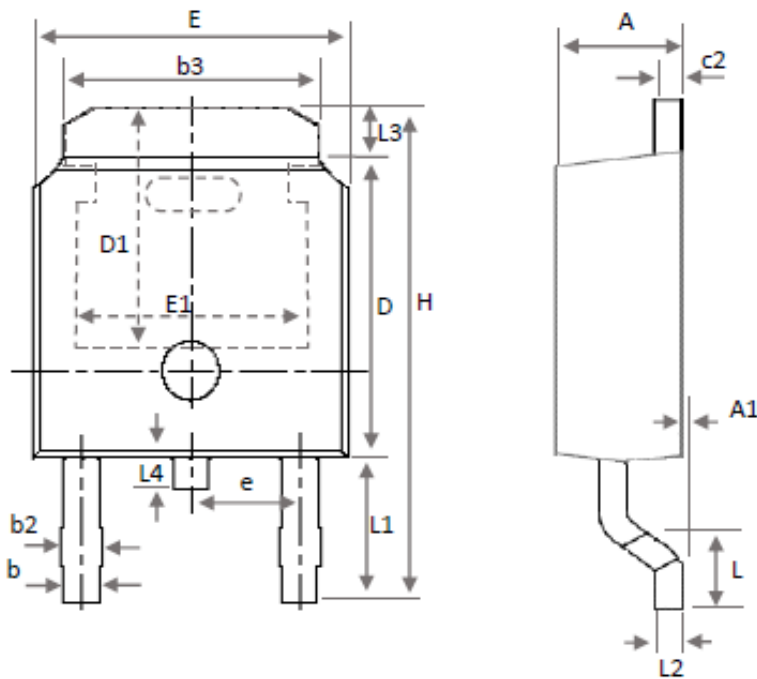
Gate Charge



Marking Information

TO-252 (D)	Marking Rule
<p>Laser Marking</p>  <p>The diagram shows a TO-252 (D) MOSFET package. On the top surface, there is a laser marking consisting of two lines of text: 'SG30N04D' on the top line and 'YYMMXXX' on the bottom line. Below the text is a small circular mark. The package has three leads extending from the bottom: a wide tab on the left, a narrow tab in the center, and a wide tab on the right.</p>	<p><u>Line 1</u> : Device Name SG30N04D</p> <p><u>Line 2</u> : Date Code YYMMXXX</p> <p>YY : Year Code MM : Month Code XXX : Serial Number</p>

Package of Dimension



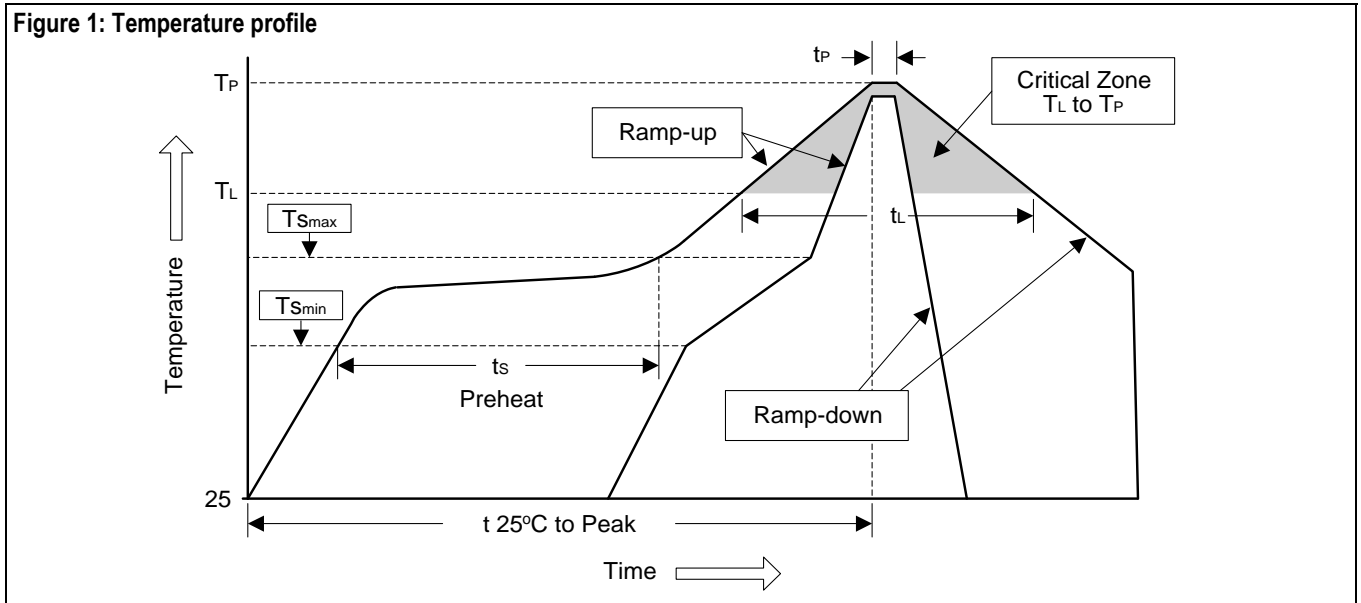
Symbol	Min	Nor	Max
E	6.35	6.54	6.731
L	1.40	1.59	1.78
L1	2.743 Ref.		
L2	0.508 BSC		
L3	0.89	1.08	1.27
L4	0.60	0.81	1.01
D	5.97	6.10	6.223
H	9.40	9.91	10.41
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	4.95	5.21	5.46
e	2.286 BSC		
A	2.18	2.29	2.39
A1	0.00	0.07	0.13
c2	0.46	0.68	0.89
D1	5.21	-	-
E1	4.32	-	-

1. All dimension are in millimeters.
2. Dimension does not include burrs and mold flash/protrusions.

Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60 to 120 sec	60 to 180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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